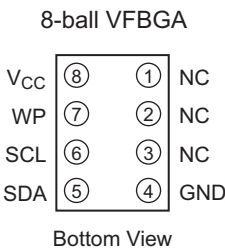
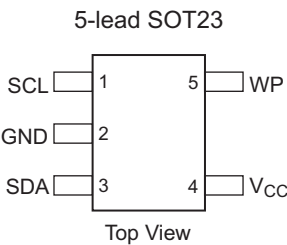
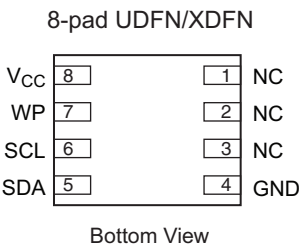
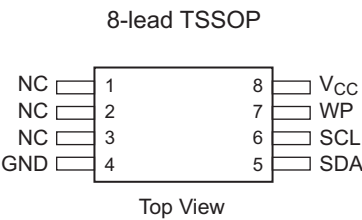
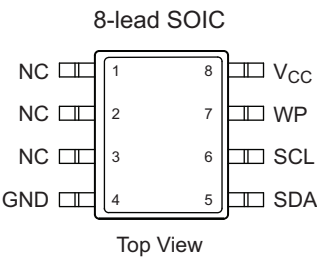
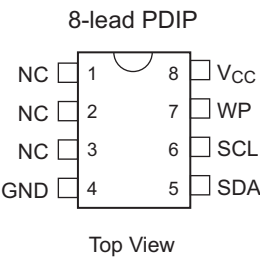


1. Pin Configurations and Pinouts

Table 1. Pin Configuration

Pin Name	Function
NC	No Connect
SDA	Serial Data
SCL	Serial Clock Input
WP	Write Protect
GND	Ground
V _{CC}	Power Supply



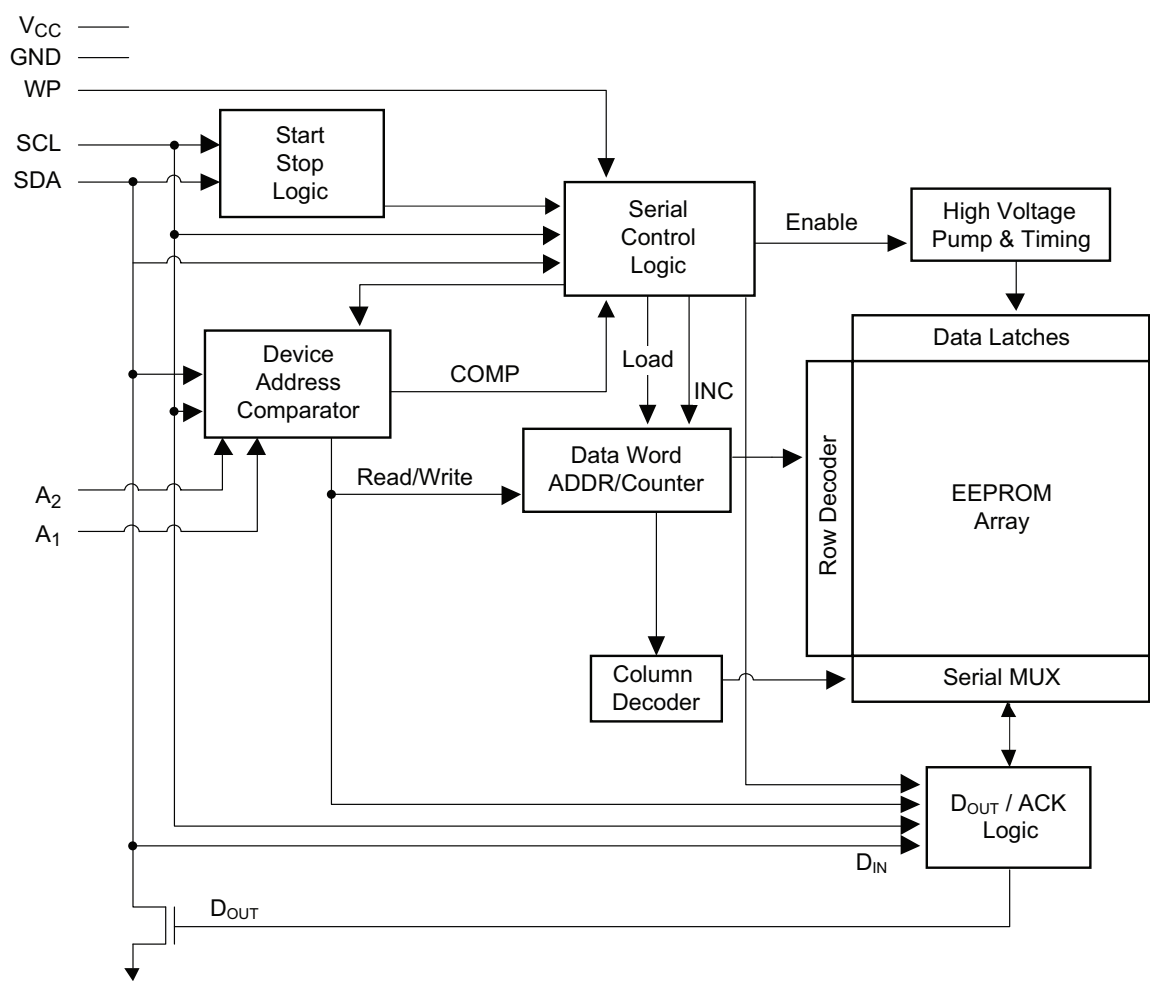
Note: Drawings are not to scale.

2. Absolute Maximum Ratings

Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on any pin with respect to ground	-1.0V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	5.0mA

*Notice: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

3. Block Diagram



4. Pin Description

Serial Clock (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

Serial Data (SDA): The SDA pin is bidirectional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

Device/Page Addresses: The AT24C16C does not use the device address pins, which limits the number of devices on a single bus to one (see [Section 7. “Device Addressing” on page 9](#)).

Write Protect (WP): AT24C16C has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal Read/Write operations when connected to Ground (GND). When the Write Protect pin is connected to V_{CC} , the Write Protection feature is enabled and operates as shown in [Table 4-1](#).

Table 4-1. Write Protect

WP Pin Status	Part of the Array Protected
At V_{CC}	Full Array
At GND	Normal Read/Write Operations

5. Memory Organization

AT24C16C, 16K Serial EEPROM: Internally organized with 128 pages of 16 bytes each, the 16K requires a 11-bit data word address for random word addressing.

5.1 Pin Capacitance

Table 5-1. Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^\circ\text{C}$, $f = 1.0\text{MHz}$, $V_{CC} = 5.5\text{V}$.

Symbol	Test Condition	Max	Units	Conditions
$C_{I/O}$	Input/Output capacitance (SDA)	8	pF	$V_{I/O} = 0\text{V}$
C_{IN}	Input capacitance ($A_0, A_1, A_2, \text{SCL}$)	6	pF	$V_{IN} = 0\text{V}$

Note: 1. This parameter is characterized and is not 100% tested.

5.2 DC Characteristics

Table 5-2. DC Characteristics

Applicable over recommended operating range from: $T_{AI} = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{CC} = 1.7\text{V}$ to 5.5V (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V_{CC1}	Supply Voltage		1.7		5.5	V
I_{CC}	Supply Current $V_{CC} = 5.0\text{V}$	Read at 100kHz		0.4	1.0	mA
I_{CC}	Supply Current $V_{CC} = 5.0\text{V}$	Write at 100kHz		2.0	3.0	mA
I_{SB1}	Standby Current $V_{CC} = 1.7\text{V}$	$V_{IN} = V_{CC}$ or V_{SS}			1.0	μA
I_{SB2}	Standby Current $V_{CC} = 5.5\text{V}$	$V_{IN} = V_{CC}$ or V_{SS}			6.0	μA
I_{LI}	Input Leakage Current	$V_{IN} = V_{CC}$ or V_{SS}		0.10	3.0	μA
I_{LO}	Output Leakage Current	$V_{OUT} = V_{CC}$ or V_{SS}		0.05	3.0	μA
V_{IL}	Input Low Level ⁽¹⁾		-0.6		$V_{CC} \times 0.3$	V
V_{IH}	Input High Level ⁽¹⁾		$V_{CC} \times 0.7$		$V_{CC} + 0.5$	V
V_{OL2}	Output Low Level $V_{CC} = 3.0\text{V}$	$I_{OL} = 2.1\text{mA}$			0.4	V
V_{OL1}	Output Low Level $V_{CC} = 1.7\text{V}$	$I_{OL} = 0.15\text{mA}$			0.2	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

5.3 AC Characteristics

Table 5-3. AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}\text{C}$ to 85°C , $V_{CC} = +1.7\text{V}$ to 5.5V , $CL = 1\text{TTL Gate and } 100\text{pF}$ (unless otherwise noted).

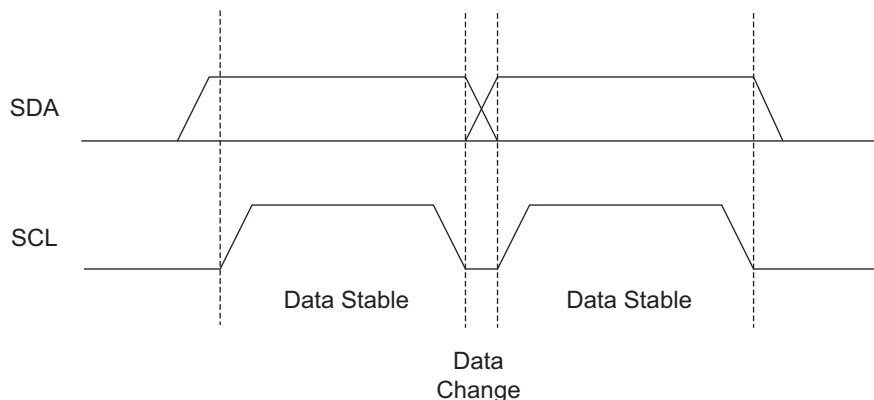
Symbol	Parameter	1.7V		2.5V, 2.7V, 5.0V		Units
		Min	Max	Min	Max	
f_{SCL}	Clock Frequency, SCL		400		1000	kHz
t_{LOW}	Clock Pulse Width Low	1.2		0.4		μs
t_{HIGH}	Clock Pulse Width High	0.6		0.4		μs
t_I	Noise Suppression Time		100		50	ns
t_{AA}	Clock Low to Data Out Valid	0.1	0.9	0.05	0.55	μs
t_{BUF}	Time the bus must be free before a new transmission can start.	1.2		0.5		μs
$t_{HD.STA}$	Start Condition Hold Time	0.6		0.25		μs
$t_{SU.STA}$	Start Condition Setup Time	0.6		0.25		μs
$t_{HD.DAT}$	Data In Hold Time	0		0		μs
$t_{SU.DAT}$	Data In Setup Time	100		100		ns
t_R	Inputs Rise Time ⁽¹⁾		0.3		0.3	μs
t_F	Inputs Fall Time ⁽¹⁾		300		100	ns
$t_{SU.STO}$	Stop Condition Setup Time	0.6		.25		μs
t_{DH}	Data Out Hold Time	50		50		ns
t_{WR}	Write Cycle Time		5		5	ms
Endurance ⁽¹⁾	3.3V, 25°C, Page Mode	1,000,000				Write Cycles

Note: 1. This parameter is ensured by characterization only.

6. Device Operation

Clock and Data Transitions: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods. Data changes during SCL high periods will indicate a Start or Stop Condition as defined below.

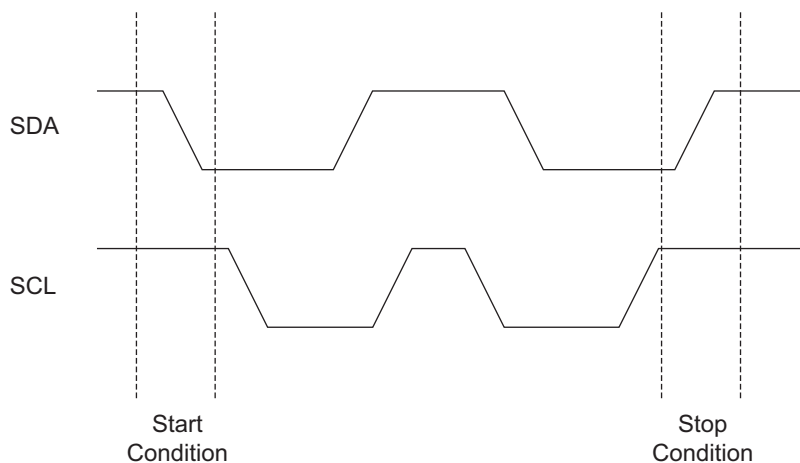
Figure 6-1. Data Validity



Start Condition: A high-to-low transition of SDA with SCL high is a Start Condition which must precede any other command.

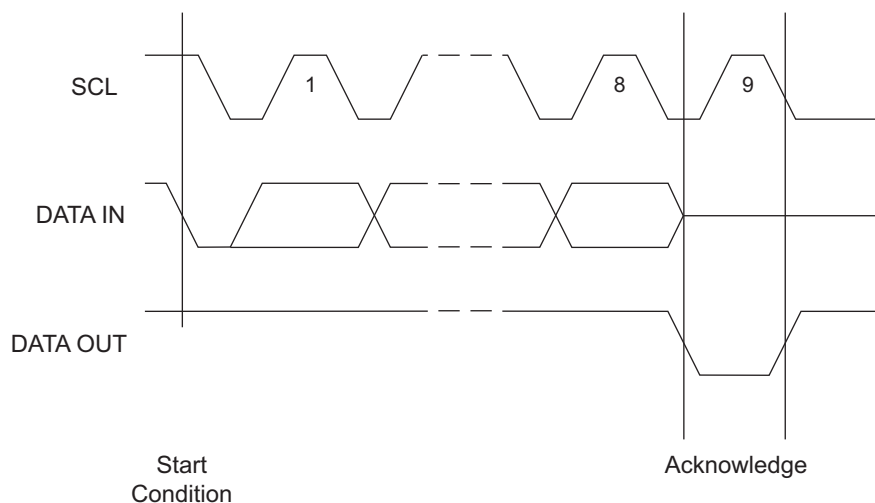
Stop Condition: A low-to-high transition of SDA with SCL high is a Stop Condition. After a read sequence, the Stop Condition command will place the EEPROM in a standby power mode.

Figure 6-2. Start Condition and Stop Condition Definition



Acknowledge: All addresses and data words are serially transmitted to and from the EEPROM in eight bit words. The EEPROM sends a zero to acknowledge that it has received each word. This happens during the ninth clock cycle.

Figure 6-3. Output Acknowledge



Standby Mode: The AT24C16C features a low-power standby mode which is enabled:

- Upon power-up.
- After the receipt of the Stop Condition and the completion of any internal operations.

2-wire Software Reset: After an interruption in protocol, power loss or system reset, any 2-wire part can be reset by following these steps:

1. Create a Start Condition (if possible).
2. Clock nine cycles.
3. Create another Start Condition followed by Stop Condition as shown below.

The device should be ready for the next communication after above steps have been completed. In the event that the device is still non-responsive or remains active on the SDA bus, a power cycle must be used to reset the device.

Figure 6-4. Software Reset

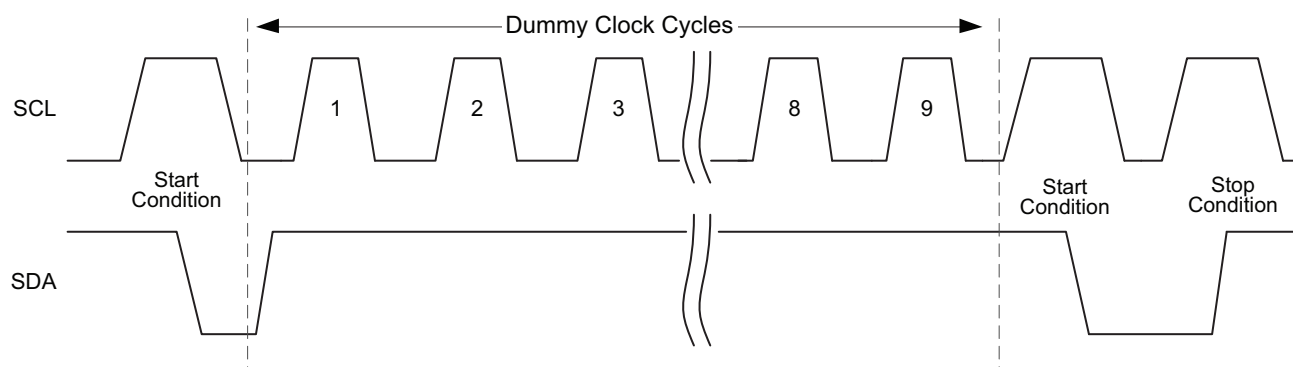


Figure 6-5. Bus Timing

SCL: Serial Clock, SDA: Serial Data I/O

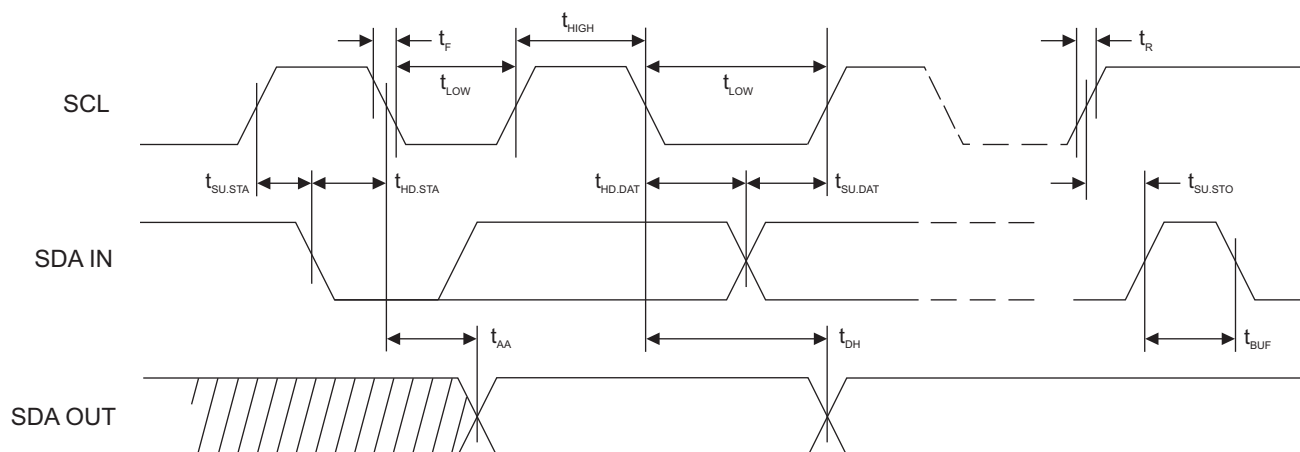
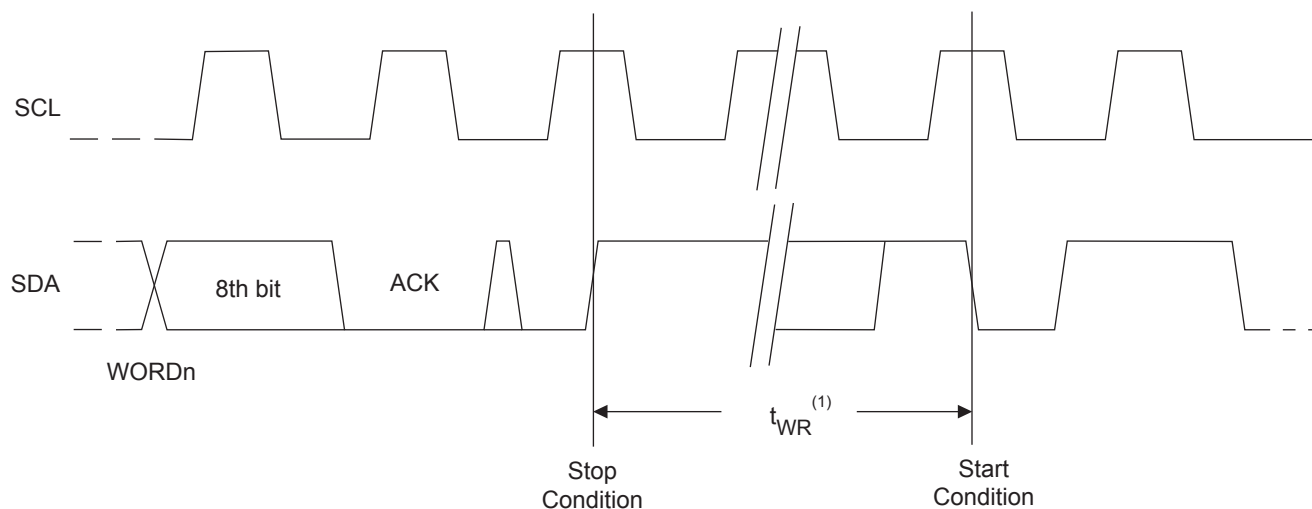


Figure 6-6. Write Cycle Timing

SCL: Serial Clock, SDA: Serial Data I/O



Note: 1. The write cycle time t_{WR} is the time from a valid Stop Condition of a Write sequence to the end of the internal clear/write cycle.

7. Device Addressing

Standard EEPROM Access: The 16K EEPROM device requires an 8-bit device address word following a Start Condition to enable the chip for a Read or Write operation. The device address word consists of a mandatory “1010” (Ah) sequence for the first four Most Significant Bits (MSB) as shown in [Figure 10. on page 12](#). This is common to all the EEPROM devices.

The next three bits used for memory page addressing are the most significant bits of the data word address which follows.

The eighth bit of the device address is the Read/Write operation select bit. A Read operation is initiated if this bit is high and a Write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the chip will return to a standby state.

Figure 7-1. Device Address

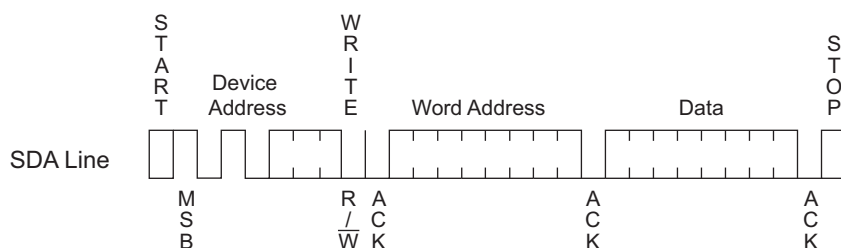
Density	Access Area	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
16K	EEPROM	1	0	1	0	P2	P1	P0	R/ $\overline{W}$

MSBLSB

8. Write Operations

Byte Write: A Write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the Write sequence with a Stop Condition. At this time the EEPROM enters an internally timed write cycle, t_{WR} , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the Write is complete.

Figure 8-1. Byte Write

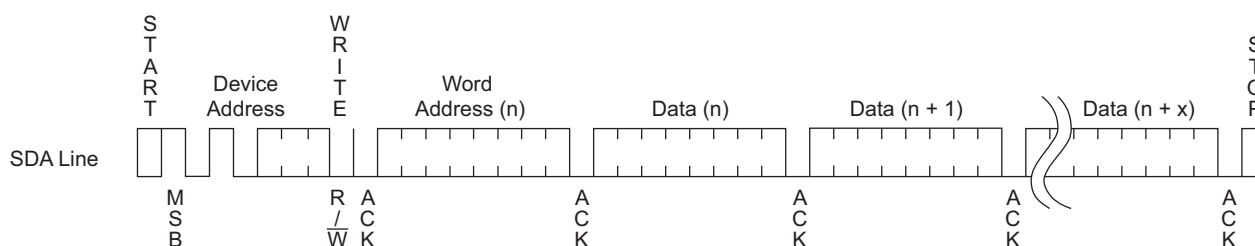


Page Write: The 16K EEPROM devices are capable of a 16-byte Page Write.

A Page Write is initiated in the same way as a Byte Write, but the microcontroller does not send a Stop Condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the Page Write sequence with a Stop Condition (see [Figure 8-2](#)).

The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than eight data words are transmitted to the EEPROM, the data word address will roll-over and previous data will be overwritten.

Figure 8-2. Page Write



Acknowledge Polling: Once the internally timed write cycle has started and the EEPROM inputs are disabled, Acknowledge Polling can be initiated. This involves sending a Start Condition followed by the device address word. The Read/Write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the Read or Write sequence to continue.

9. Read Operations

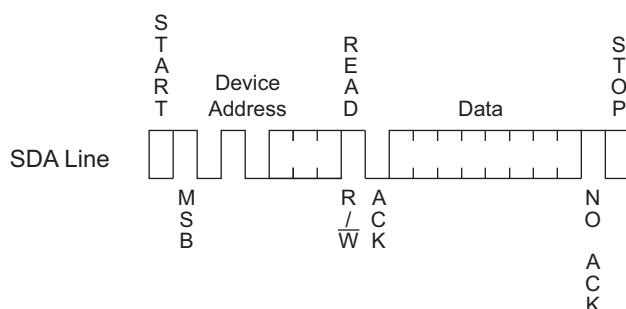
Read operations are initiated in the same way as Write operations with the exception that the Read/Write select bit in the device address word is set to one. There are three read operations:

- Current Address Read
- Random Address Read
- Sequential Read.

Current Address Read: The internal data word address counter maintains the last address accessed during the last Read or Write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address roll-over during Read is from the last byte of the last memory page to the first byte of the first page. The address roll-over during Write is from the last byte of the current page to the first byte of the same page.

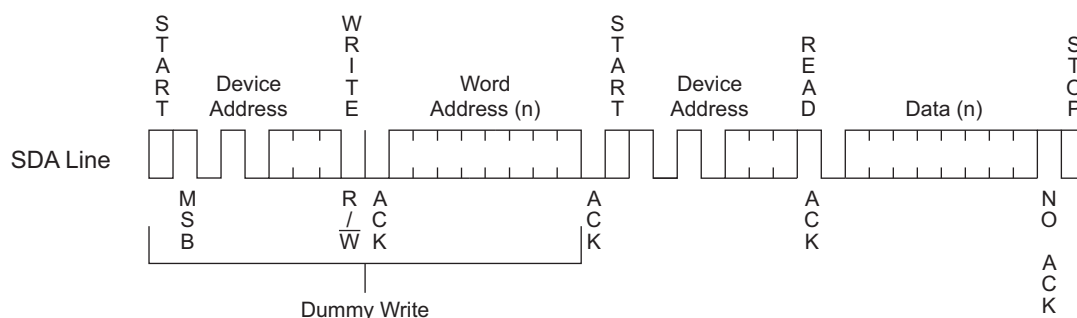
Once the device address with the Read/Write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following Stop Condition (see [Figure 9-1](#)).

Figure 9-1. Current Address Read



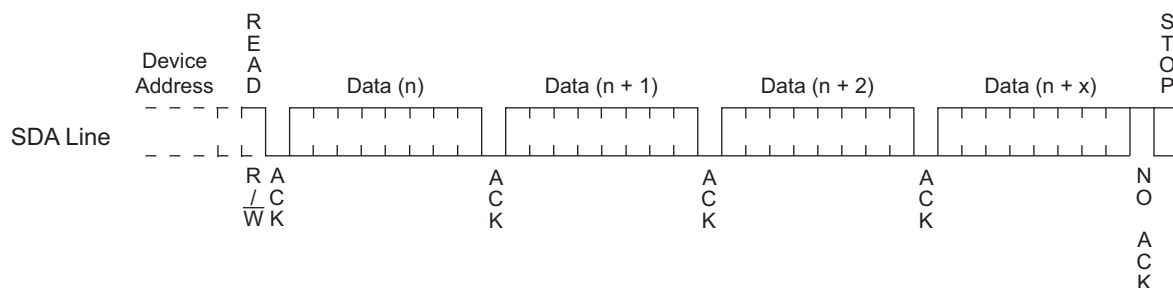
Random Read: A Random Read requires a Dummy Byte Write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another Start Condition. The microcontroller now initiates a Current Address Read by sending a device address with the Read/Write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following Stop Condition.

Figure 9-2. Random Read

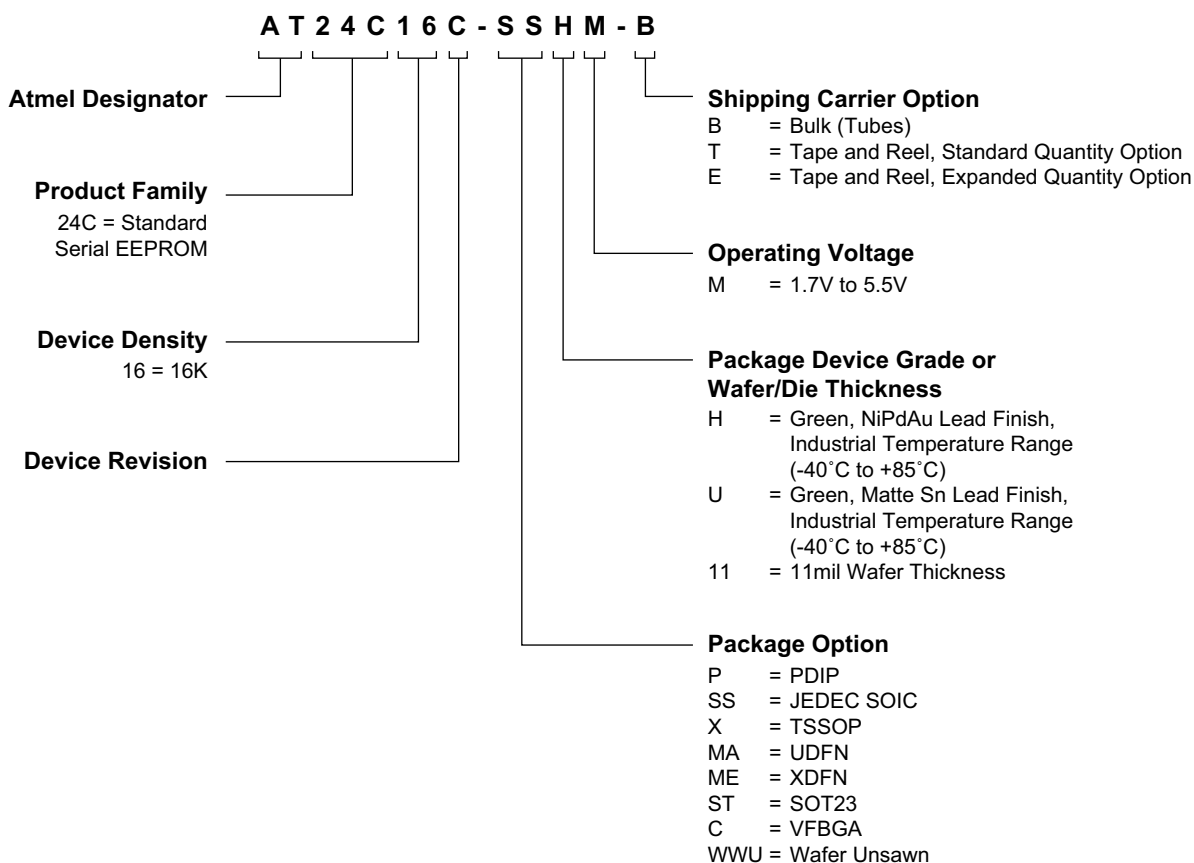


Sequential Read: Sequential Reads are initiated by either a Current Address Read or a Random Address Read. After the microcontroller receives a data word, it responds with an Acknowledge. As long as the EEPROM receives an Acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will roll-over and the Sequential Read will continue. The Sequential Read operation is terminated when the microcontroller does not respond with a zero but does generate a following Stop Condition.

Figure 9-3. Sequential Read



10. Ordering Code Detail



11. Product Markings

AT24C16C: Package Marking Information

8-lead PDIP	8-lead SOIC	8-lead TSSOP	8-pad UDFN
8-pad XDFN	5-lead SOT-23	8-ball VFBGA	

Note 1: ● designates pin 1

Note 2: Package drawings are not to scale

Note 3: For SOT23 package with date codes before 7B, the bottom line (YMXX) is marked on the bottom side and there is no Country of Assembly (@) mark on the top line.

Catalog Number Truncation				
AT24C16C		Truncation Code ###: 16C / #: AC		
Date Codes			Voltages	
Y = Year	M = Month	WW = Work Week of Assembly	% = Minimum Voltage	
6: 2016	0: 2020	A: January	M: 1.7V min	
7: 2017	1: 2021	B: February		
8: 2018	2: 2022			
9: 2019	3: 2023	L: December		
Country of Assembly		Lot Number	Grade/Lead Finish Material	
@ = Country of Assembly		AAA...A = Atmel Wafer Lot Number	H: Industrial/NiPdAu U: Industrial/Matte Tin/SnAgCu	
Trace Code			Atmel Truncation	
XX = Trace Code (Atmel Lot Numbers Correspond to Code) Example: AA, AB.... YZ, ZZ			AT: Atmel ATM: Atmel ATML: Atmel	

12/6/16

 Package Mark Contact: DL-CSO-Assy_eng@atmel.com	TITLE	DRAWING NO.	REV.
	24C16CSM, AT24C16C Package Marking Information	24C16CSM	E

12. Ordering Information

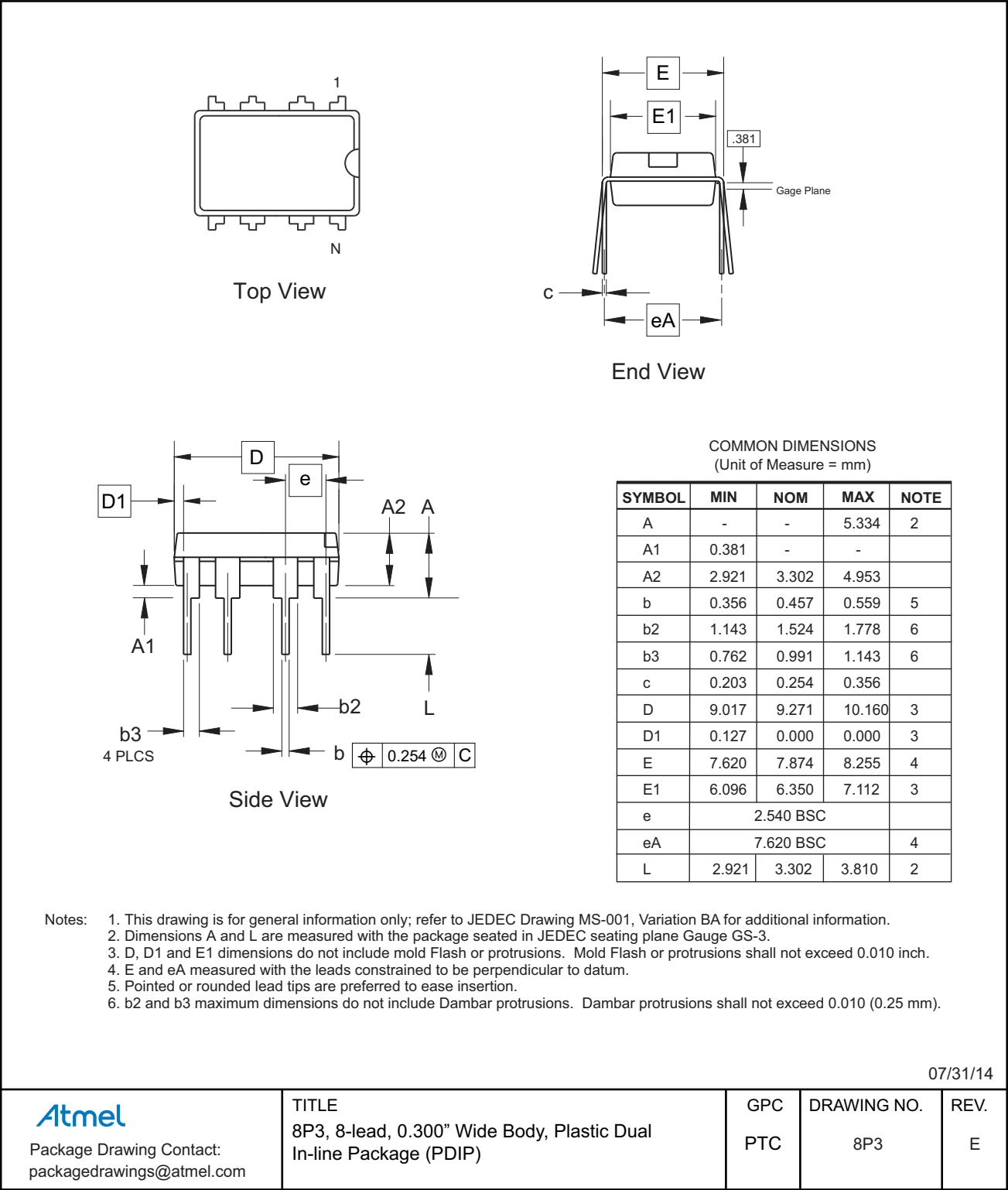
Atmel Ordering Code	Lead Finish	Package	Delivery Information		Operation Range
			Form	Quantity	
AT24C16C-SSHM-B	NiPdAu (Lead-free/Halogen-free)	8S1	Bulk (Tubes)	100 per Tube	Industrial Temperature (-40°C to 85°C)
AT24C16C-SSHM-T			Tape and Reel	4,000 per Reel	
AT24C16C-XHM-B		8X	Bulk (Tubes)	100 per Tube	
AT24C16C-XHM-T			Tape and Reel	5,000 per Reel	
AT24C16C-MAHM-T		8MA2	Tape and Reel	5,000 per Reel	
AT24C16C-MAHM-E			Tape and Reel	15,000 per Reel	
AT24C16C-PUM	Matte Sn (Lead-free/Halogen-free)	8P3	Bulk (Tubes)	50 per Tube	
AT24C16C-STUM-T		5TS1	Tape and Reel	5,000 per Reel	
AT24C16C-CUM-T	SnAgCu (Lead-free/Halogen-free)	8U3-1	Tape and Reel	5,000 per Reel	
AT24C16C-MEHM-T	N/A	8ME1	Tape and Reel	5,000 per Reel	
AT24C16C-WWU11M ⁽¹⁾	N/A	Wafer Sale	Note 1		

Note: 1. For Wafer sales, please contact Atmel Sales.

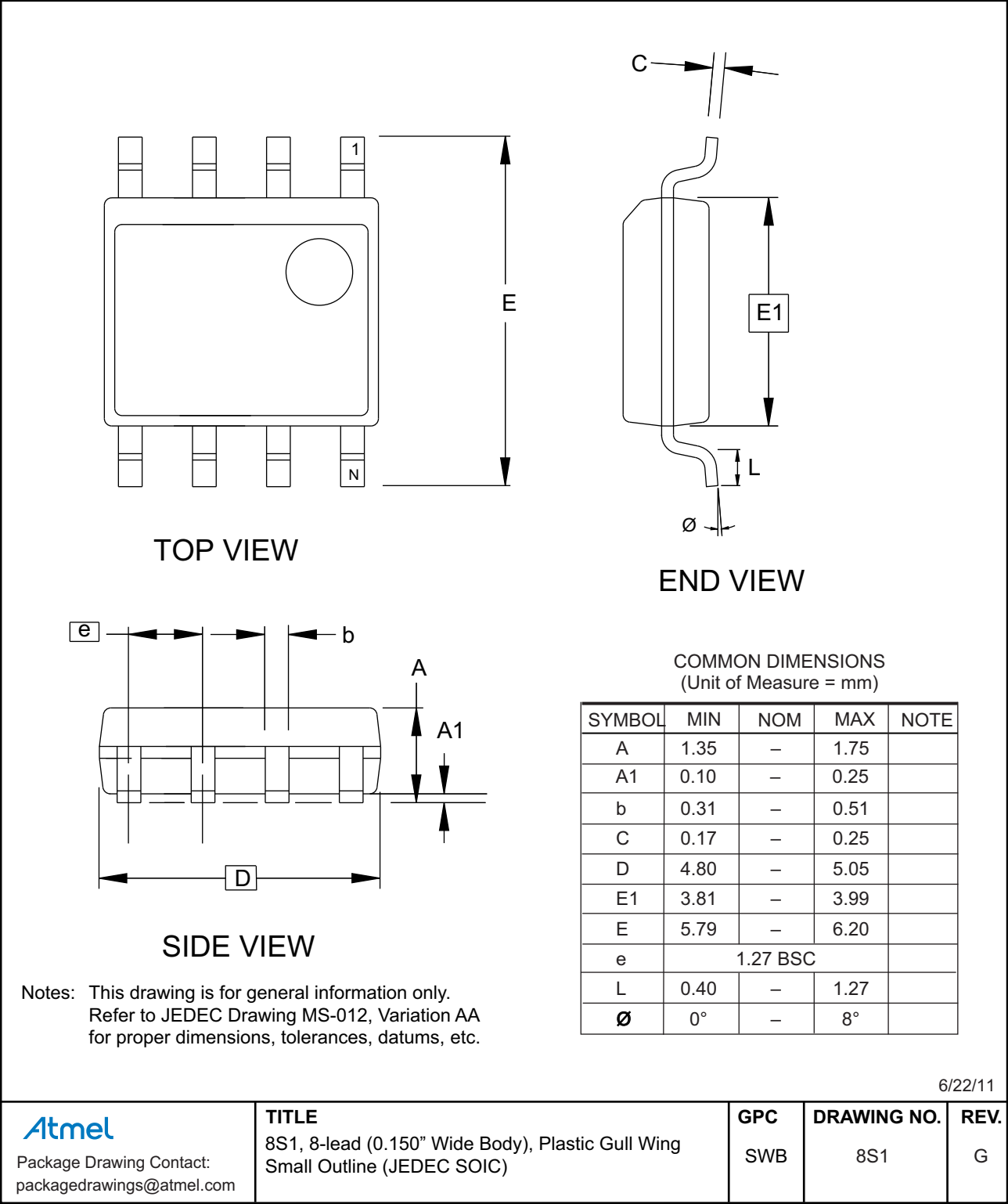
Package Type	
8P3	8-lead, 0.300" wide, Plastic Dual Inline Package (PDIP)
8S1	8-lead, 0.150" wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
8X	8-lead, 4.40mm body, Plastic Thin Shrink Small Outline Package (TSSOP)
8MA2	8-pad, 2.00mm x 3.00mm body, 0.50mm pitch, Plastic Ultra Thin Dual Flat No Lead (UDFN)
8ME1	8-lead, 1.80mm x 2.20mm body, 0.40mm pitch, Extra Thin Dual Flat No Lead (XDFN)
5TS1	5-lead, 2.90mm x 1.60mm body, Plastic Thin Shrink Small Outline (SOT23)
8U3-1	8-ball, 1.50mm x 2.00mm body, 0.50mm pitch, Die Ball Grid Array (VFBGA)

13. Packaging Information

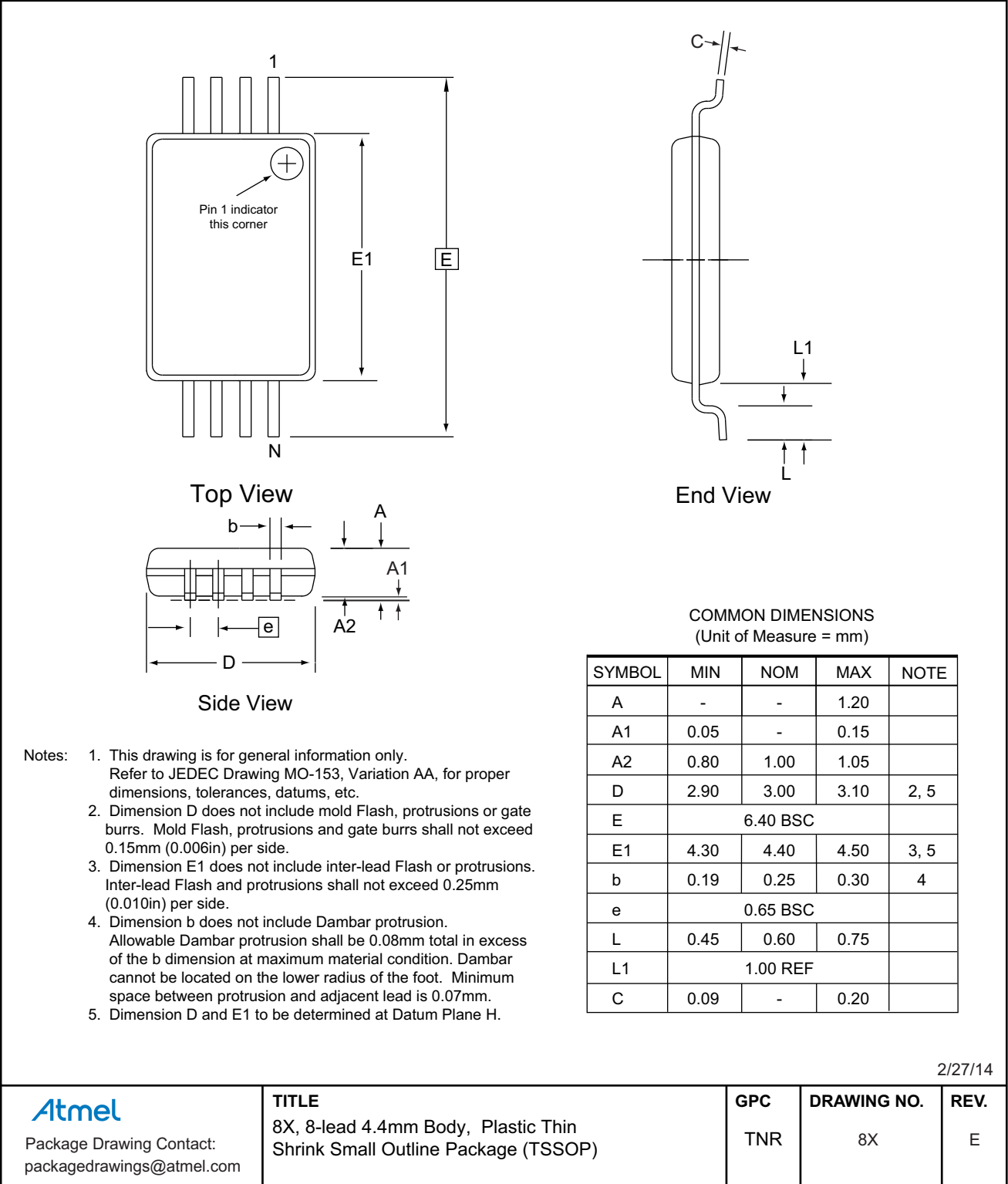
13.1 8P3 — 8-lead PDIP



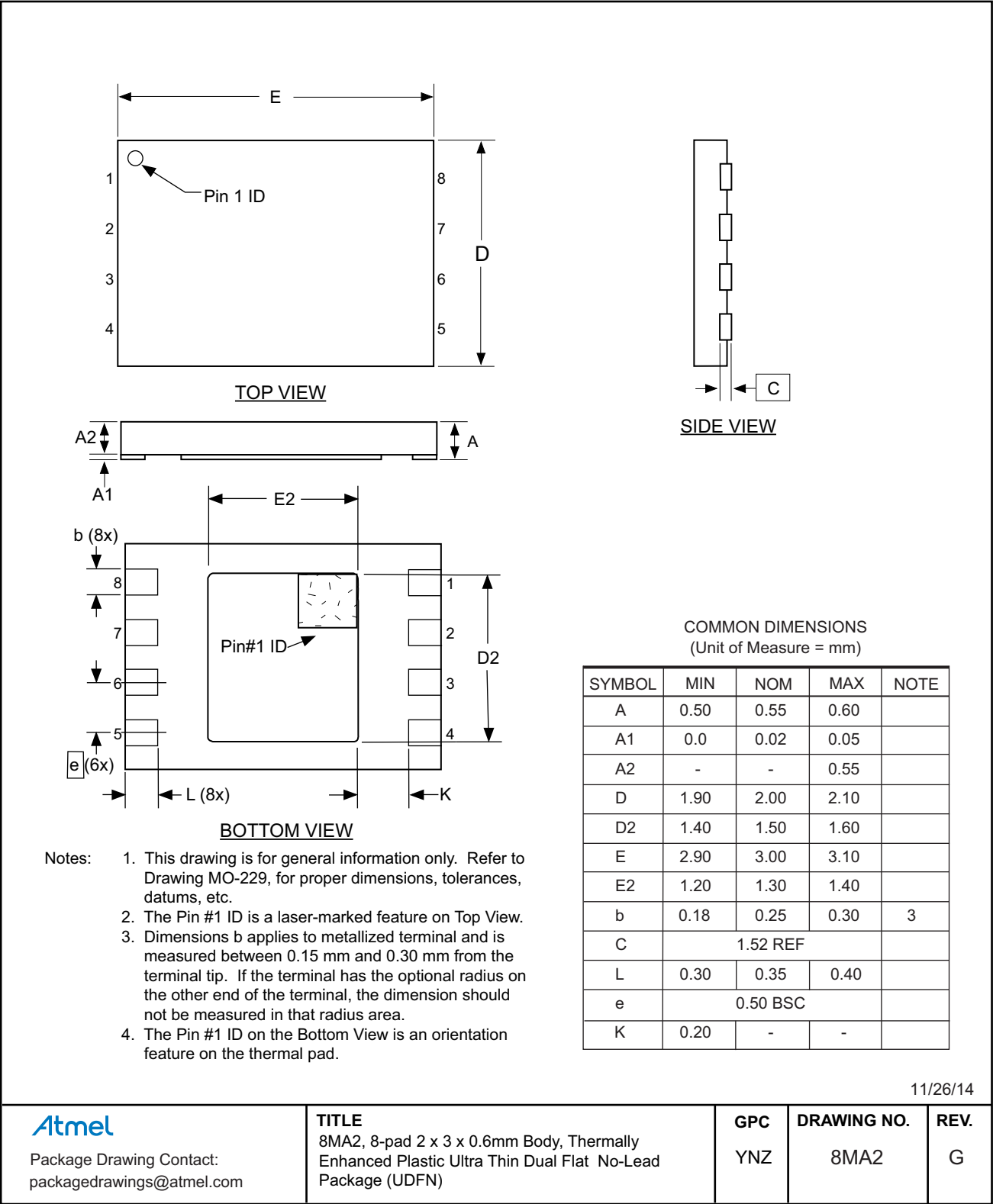
13.2 8S1 — 8-lead JEDEC SOIC



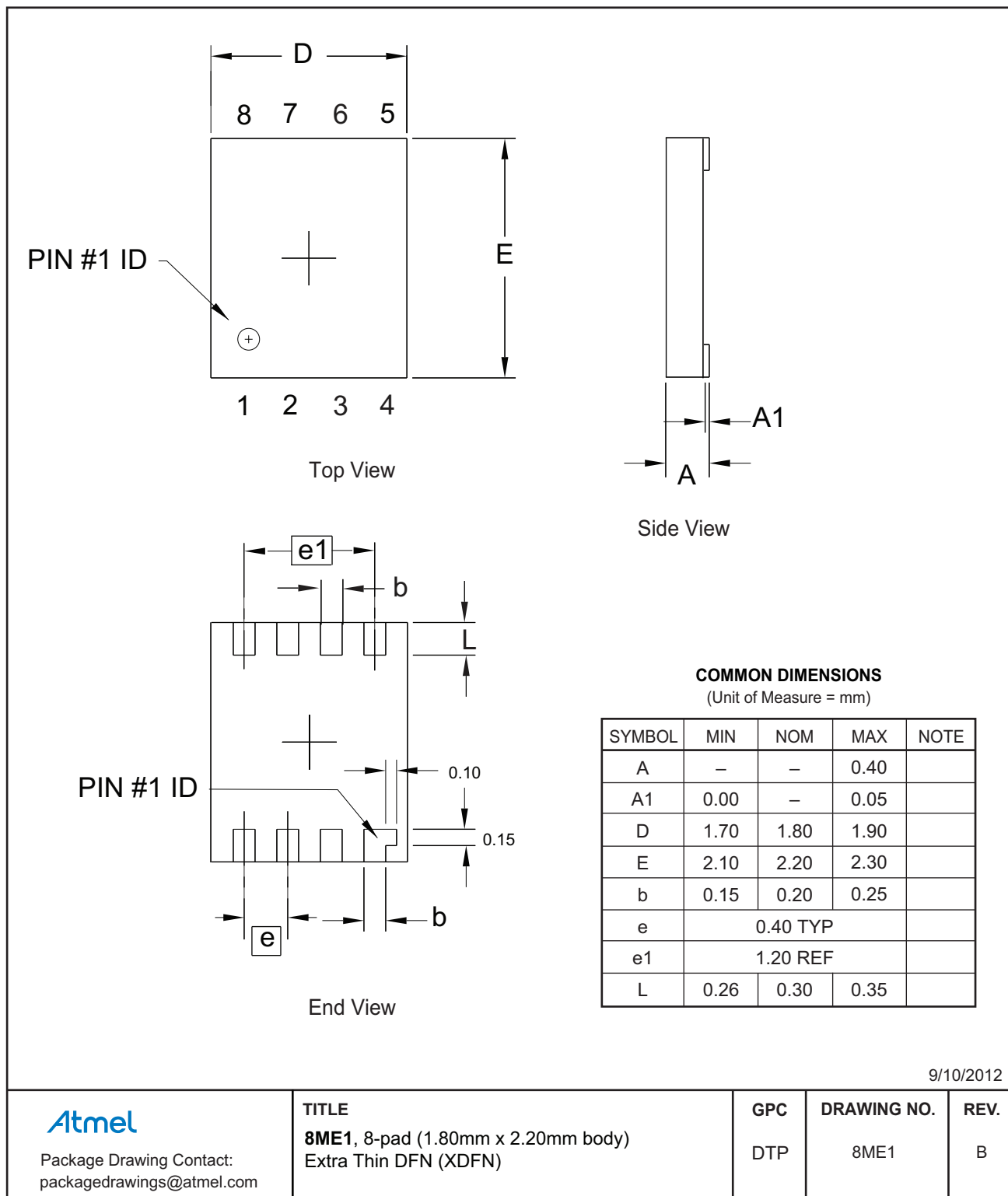
13.3 8X — 8-lead TSSOP



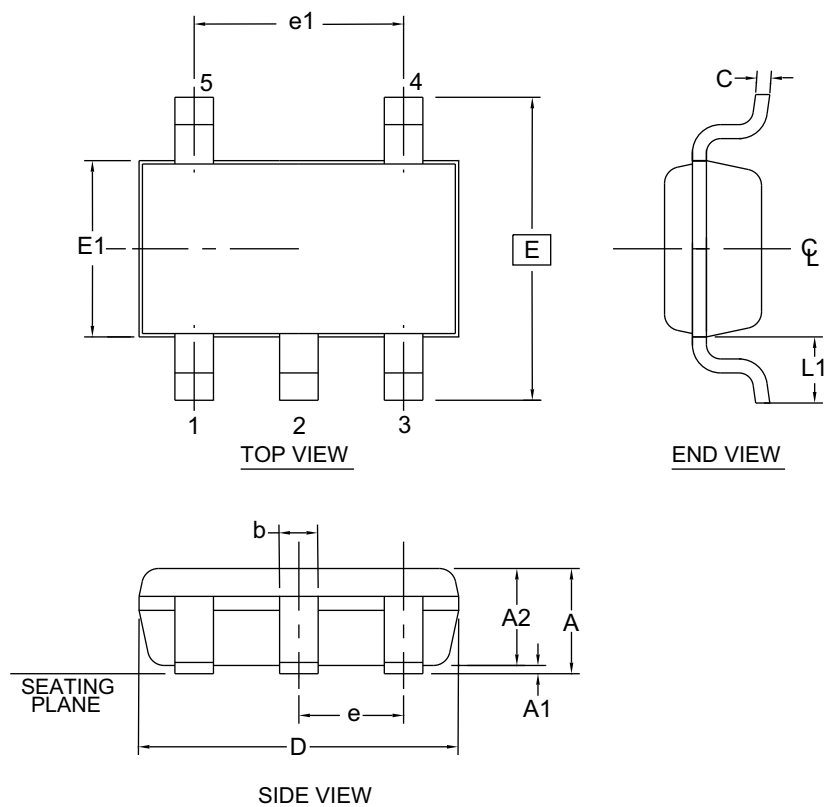
13.4 8MA2 — 8-pad UDFN



13.5 8ME1 — 8-pad XDFN



13.6 5TS1 — 5-lead SOT23



1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.15 mm per side.
2. The package top may be smaller than the package bottom. Dimensions D and E1 are determined at the outermost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.
4. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall be 0.08 mm total in excess of the "b" dimension at maximum material condition. The dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and an adjacent lead shall not be less than 0.07 mm.

This drawing is for general information only. Refer to JEDEC Drawing MO-193, Variation AB for additional information.

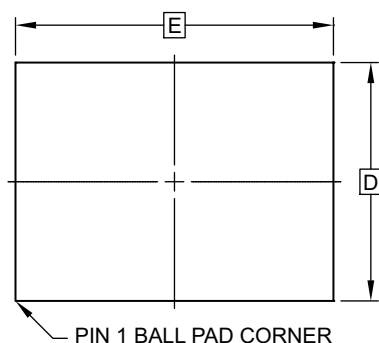
COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	-	-	1.00	
A1	0.00	-	0.10	
A2	0.70	0.90	1.00	
c	0.08	-	0.20	3
D	2.90 BSC			1,2
E	2.80 BSC			1,2
E1	1.60 BSC			1,2
L1	0.60 REF			
e	0.95 BSC			
e1	1.90 BSC			
b	0.30	-	0.50	3,4

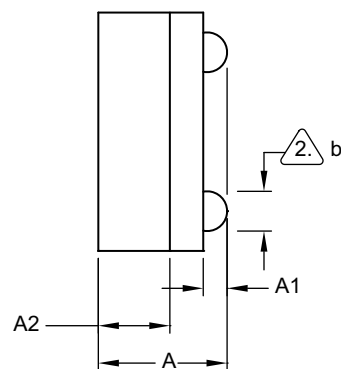
5/31/12

Atmel Package Drawing Contact: packagedrawings@atmel.com	TITLE 5TS1, 5-lead 1.60mm Body, Plastic Thin Shrink Small Outline Package (Shrink SOT)	GPC	DRAWING NO.	REV.
		TSZ	5TS1	D

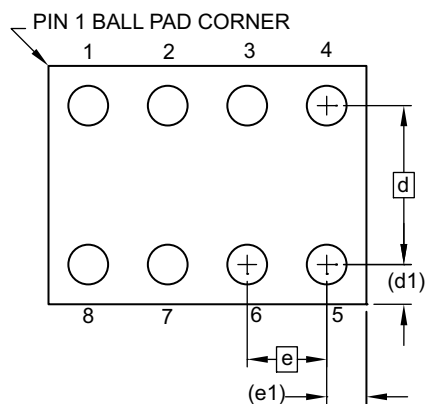
13.7 8U3-1 — 8-ball VFBGA



TOP VIEW



SIDE VIEW



BOTTOM VIEW
8 SOLDER BALLS

Notes:

1. This drawing is for general information only.
2. Dimension 'b' is measured at maximum solder ball diameter.
3. Solder ball composition shall be 95.5Sn-4.0Ag-.5Cu.

COMMON DIMENSIONS
(Unit of Measure - mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.73	0.79	0.85	
A1	0.09	0.14	0.19	
A2	0.40	0.45	0.50	
b	0.20	0.25	0.30	2
D	1.50 BSC			
E	2.0 BSC			
e	0.50 BSC			
e1	0.25 REF			
d	1.00 BSC			
d1	0.25 REF			

6/11/13



Package Drawing Contact:
packagedrawings@atmel.com

TITLE

8U3-1, 8-ball, 1.50mm x 2.00mm body, 0.50mm pitch,
Very Thin, Fine-Pitch Ball Grid Array Package (VFBGA)

GPC

GXU

DRAWING NO.

8U3-1

REV.

F

14. Revision History

Doc. Rev.	Date	Comments
8719D	12/2016	Part marking SOT23: - Moved backside mark (YMXX) to front side line2. - Added @ = Country of Assembly.
8719C	01/2015	Add the UDFN Expanded Quantity Option. Update the 8X, 8MA2, 8P3, and 8U3-1 package outline drawings, the ordering information section, and the disclaimer page.
8719B	07/2013	Minor grammatical corrections. Update Atmel logos and template.
8719A	09/2010	Initial document release.

